4-bit dual supply translating transceiver with configurable voltage translation; 3-state

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Product data sheet

1. General description

The 74AVCH4T245 is a 4-bit, dual supply transceiver that enables bidirectional level translation. The device can be used as two 2-bit transceivers or as a 4-bit transceiver. It features two 2-bit input-output ports (nAn and nBn), a direction control input (nDIR), a output enable input (nOE) and dual supply pins ($V_{CC(A)}$ and $V_{CC(B)}$). Both $V_{CC(A)}$ and $V_{CC(B)}$ can be supplied at any voltage between 0.8 V and 3.6 V making the device suitable for translating between any of the low voltage nodes (0.8 V, 1.2 V, 1.5 V, 1.8 V, 2.5 V and 3.3 V). Pins nAn, nOE and nDIR are referenced to $V_{CC(A)}$ and pins nBn are referenced to $V_{CC(B)}$. A HIGH on nDIR allows transmission from nAn to nBn and a LOW on nDIR allows transmission from nBn to nAn. The output enable input (nOE) can be used to disable the outputs so the buses are effectively isolated.

The device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing any damaging backflow current through the device when it is powered down. In suspend mode when either $V_{CC(A)}$ or $V_{CC(B)}$ are at GND level, both nAn and nBn outputs are in the high-impedance OFF-state. The bus hold circuitry on the powered-up side always stays active.

The 74AVCH4T245 has active bus hold circuitry which is provided to hold unused or floating data inputs at a valid logic level. This feature eliminates the need for external pull-up or pull-down resistors.

2. Features and benefits

- Wide supply voltage range:
 - V_{CC(A)}: 0.8 V to 3.6 V
 - V_{CC(B)}: 0.8 V to 3.6 V
- Complies with JEDEC standards:
 - JESD8-12 (0.8 V to 1.3 V)
 - JESD8-11 (0.9 V to 1.65 V)
 - ◆ JESD8-7 (1.2 V to 1.95 V)
 - JESD8-5 (1.8 V to 2.7 V)
 - JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - HBM JESD22-A114E Class 3B exceeds 8000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101C exceeds 1000 V
- Maximum data rates:
 - ◆ 380 Mbit/s (≥ 1.8 V to 3.3 V translation)

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- ◆ 200 Mbit/s (≥ 1.1 V to 3.3 V translation)
- ◆ 200 Mbit/s (≥ 1.1 V to 2.5 V translation)
- 200 Mbit/s (\geq 1.1 V to 1.8 V translation)
- 150 Mbit/s (\geq 1.1 V to 1.5 V translation)
- ◆ 100 Mbit/s (≥ 1.1 V to 1.2 V translation)
- Suspend mode
- Bus hold on data inputs
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C

3. Ordering information

Table 1.Ordering information

Type number	Package								
	Temperature range	Name	Description	Version					
74AVCH4T245D	–40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1					
74AVCH4T245PW	–40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1					
74AVCH4T245BQ	–40 °C to +125 °C	DHVQFN16	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body $2.5 \times 3.5 \times 0.85$ mm	SOT763-1					
74AVCH4T245GU	–40 °C to +125 °C	XQFN16	plastic, extremely thin quad flat package; no leads; 16 terminals; body $1.80 \times 2.60 \times 0.50$ mm	SOT1161-1					

4. Marking

Table 2.Marking codes

Type number	Marking code
74AVCH4T245D	74AVCH4T245D
74AVCH4T245PW	CH4T245
74AVCH4T245BQ	H4T245
74AVCH4T245GU	К4

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5. Functional diagram





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6. Pinning information

6.1 Pinning





6.2 Pin description

Table 3. Pin d	lescription		
Symbol	Pin		Description
	SOT109-1, SOT403-1 and SOT763-1	SOT1161-1	
V _{CC(A)}	1	3	supply voltage A (nAn, n $\overline{\text{OE}}$ and nDIR inputs are referenced to $V_{\text{CC}(A)})$
1DIR, 2DIR	2, 3	4, 5	direction control
1A1, 1A2	4, 5	6, 7	data input or output
2A1, 2A2	6, 7	8, 9	data input or output
GND ^[1]	8, 9	10, 11	ground (0 V)
2B2, 2B1	10, 11	12, 13	data input or output
1B2, 1B1	12, 13	14, 15	data input or output
2 <u>0E</u> , 1 <u>0E</u>	14, 15	16, 1	output enable input (active LOW)
V _{CC(B)}	16	2	supply voltage B (nBn inputs are referenced to $V_{\mbox{CC}(B)}$

[1] All GND pins must be connected to ground (0 V).

7. Functional description

Table 4.Function table

Supply voltage	Input		Input/output ^[3]		
V _{CC(A)} , V _{CC(B)}	nOE ^[2]	nDIR ^[2]	nAn <mark>[2]</mark>	nBn <mark>[2]</mark>	
0.8 V to 3.6 V	L	L	nAn = nBn	input	
0.8 V to 3.6 V	L	Н	input	nBn = nAn	
0.8 V to 3.6 V	Н	Х	Z	Z	
GND ^[3]	Х	Х	Z	Z	

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

[2] The nAn, nDIR and n \overline{OE} input circuit is referenced to V_{CC(A)}; The nBn input circuit is referenced to V_{CC(B)}.

[3] If at least one of $V_{CC(A)}$ or $V_{CC(B)}$ is at GND level, the device goes into suspend mode.

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CC(A)}	supply voltage A			-0.5	+4.6	V
V _{CC(B)}	supply voltage B			-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V		-50	-	mA
VI	input voltage		[1]	-0.5	+4.6	V
I _{ОК}	output clamping current	V _O < 0 V		-50	-	mA
Vo	output voltage	Active mode	[1][2][3]	-0.5	$V_{CCO} + 0.5$	V
		Suspend or 3-state mode	[1]	-0.5	+4.6	V
I _O	output current	$V_{O} = 0 V$ to V_{CCO}	[2]	-	±50	mA
I _{CC}	supply current	per $V_{CC(A)}$ or $V_{CC(B)}$ pin		-	100	mA
I _{GND}	ground current	per GND pin		-100	-	mA
T _{stg}	storage temperature			-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \ to \ +125 \ ^{\circ}C$				
		SO16, TSSOP16 and DHVQFN16	[4]	-	500	mW
		XQFN16	[5]	-	250	mW

[1] The minimum input voltage ratings and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] V_{CCO} is the supply voltage associated with the output port.

[3] V_{CCO} + 0.5 V should not exceed 4.6 V.

[4] For SO16 package: above 70 °C the value of Ptot derates linearly at 8 mW/K.

For TSSOP16 package: above 60 °C the value of P_{tot} derates linearly at 5.5 mW/K. For DHVQFN16 package: above 60 °C the value of P_{tot} derates linearly at 4.5 mW/K.

[5] For XQFN16 package: above 133 °C the value of P_{tot} derates linearly with 14.5 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CC(A)}	supply voltage A			0.8	3.6	V
V _{CC(B)}	supply voltage B			0.8	3.6	V
VI	input voltage			0	3.6	V
Vo	output voltage	Active mode	[1]	0	V _{CCO}	V
		Suspend or 3-state mode		0	3.6	V
T _{amb}	ambient temperature			-40	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	$V_{CCI} = 0.8 \text{ V} \text{ to } 3.6 \text{ V}$	[2]	-	5	ns/V

[1] V_{CCO} is the supply voltage associated with the output port.

[2] V_{CCI} is the supply voltage associated with the input port.

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10. Static characteristics

Table 7. Typical static characteristics at $T_{amb} = 25 \text{ °C}[1][2]$

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{OH}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$					
		$I_{O} = -1.5 \text{ mA}; V_{CC(A)} = V_{CC(B)} = 0.8 \text{ V}$		-	0.69	-	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$					
		I_{O} = 1.5 mA; $V_{CC(A)} = V_{CC(B)} = 0.8 V$		-	0.07	-	V
lı	input leakage current	nDIR, n \overline{OE} input; V _I = 0 V or 3.6 V; V _{CC(A)} = V _{CC(B)} = 0.8 V to 3.6 V		-	±0.025	±0.25	μΑ
I _{BHL}	bus hold LOW current	A or B port; $V_I = 0.42$ V; $V_{CC(A)} = V_{CC(B)} = 1.2$ V	[3]	-	26	-	μΑ
I _{BHH}	bus hold HIGH current	A or B port; $V_I = 0.78$ V; $V_{CC(A)} = V_{CC(B)} = 1.2$ V	<u>[4]</u>	-	-24	-	μΑ
I _{BHLO}	bus hold LOW overdrive current	A or B port; $V_{CC(A)} = V_{CC(B)} = 1.2 V$	[5]	-	27	-	μΑ
I _{BHHO}	bus hold HIGH overdrive current	A or B port; $V_{CC(A)} = V_{CC(B)} = 1.2 V$	[6]	-	-26	-	μA
I _{OZ}	OFF-state output current	A or B port; $V_O = 0$ V or V_{CCO} ; $V_{CC(A)} = V_{CC(B)} = 3.6$ V	[7]	-	±0.5	±2.5	μΑ
		suspend mode A port; $V_O = 0$ V or V_{CCO} ; $V_{CC(A)} = 3.6$ V; $V_{CC(B)} = 0$ V	[7]	-	±0.5	±2.5	μΑ
		suspend mode B port; $V_O = 0$ V or V_{CCO} ; $V_{CC(A)} = 0$ V; $V_{CC(B)} = 3.6$ V	[7]	-	±0.5	±2.5	μA
I _{OFF}	power-off leakage current	A port; V ₁ or V _O = 0 V to 3.6 V; V _{CC(A)} = 0 V; V _{CC(B)} = 0.8 V to 3.6 V		-	±0.1	±1	μΑ
		B port; V ₁ or V _O = 0 V to 3.6 V; V _{CC(B)} = 0 V; V _{CC(A)} = 0.8 V to 3.6 V		-	±0.1	±1	μΑ
Cı	input capacitance	nDIR, n $\overline{\text{OE}}$ input; V _I = 0 V or 3.3 V; V _{CC(A)} = V _{CC(B)} = 3.3 V		-	1.0	-	pF
C _{I/O}	input/output capacitance	A and B port; $V_0 = 3.3$ V or 0 V; $V_{CC(A)} = V_{CC(B)} = 3.3$ V		-	4.0	-	pF

[1] V_{CCO} is the supply voltage associated with the output port.

[2] V_{CCI} is the supply voltage associated with the data input port.

[3] The bus hold circuit can sink at least the minimum low sustaining current at V_{IL} max. I_{BHL} should be measured after lowering V_I to GND and then raising it to V_{IL} max.

[4] The bus hold circuit can source at least the minimum high sustaining current at V_{IH} min. I_{BHH} should be measured after raising V_I to V_{CC} and then lowering it to V_{IH} min.

[5] An external driver must source at least I_{BHLO} to switch this node from LOW to HIGH.

[6] An external driver must sink at least I_{BHHO} to switch this node from HIGH to LOW.

[7] For I/O ports, the parameter I_{OZ} includes the input leakage current.

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Table 8. Static characteristics [1][2]

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol Parameter		Conditions	-40 °	C to +85	5 °C	–40 °C to +125 °C		Unit
			Min	ſ	Max	Min	Max	
V _{IH}	HIGH-level	data input						
	input voltage	V _{CCI} = 0.8 V	0.70V _C	СІ	-	0.70V _{CCI}	-	V
		V _{CCI} = 1.1 V to 1.95 V	0.65V _C	СІ	-	0.65V _{CCI}	-	V
		$V_{CCI} = 2.3 \text{ V to } 2.7 \text{ V}$	1.6		-	1.6	-	V
		$V_{CCI} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2		-	2	-	V
		nDIR, nOE input						
		V _{CC(A)} = 0.8 V	0.70V _{CC}	C(A)	-	0.70V _{CC(A)}	-	V
		V _{CC(A)} = 1.1 V to 1.95 V	0.65V _{CC}	C(A)	-	0.65V _{CC(A)}	-	V
		V _{CC(A)} = 2.3 V to 2.7 V	1.6		-	1.6	-	V
		V _{CC(A)} = 3.0 V to 3.6 V	2		-	2	-	V
V _{IL}	LOW-level	data input						
	input voltage	V _{CCI} = 0.8 V	-	0.3	0V _{CCI}	-	0.30V _{CCI}	V
		V _{CCI} = 1.1 V to 1.95 V	-	0.3	5V _{CCI}	-	0.35V _{CCI}	V
		$V_{CCI} = 2.3 \text{ V to } 2.7 \text{ V}$	-		0.7	-	0.7	V
		V _{CCI} = 3.0 V to 3.6 V	-		0.8	-	0.8	V
		nDIR, nOE input						
		V _{CC(A)} = 0.8 V	-	0.30	OV _{CC(A)}	-	0.30V _{CC(A)}	V
		V _{CC(A)} = 1.1 V to 1.95 V	-	0.35	5V _{CC(A)}	-	0.35V _{CC(A)}	V
		V _{CC(A)} = 2.3 V to 2.7 V	-		0.7	-	0.7	V
		V _{CC(A)} = 3.0 V to 3.6 V	-		0.8	-	0.8	V
V _{OH}	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}$						
	output voltage	$ I_O = -100 \ \mu \text{A}; \\ V_{CC(\text{A})} = V_{CC(\text{B})} = 0.8 \ \text{V to } 3.6 \ \text{V} $	V _{CCO} – 0	D.1	-	V _{CCO} – 0.1	-	V
		$I_{O} = -3 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 1.1 \text{ V}$	0.85		-	0.85	-	V
		$I_{O} = -6 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 1.4 \text{ V}$	1.05		-	1.05	-	V
		$I_{O} = -8 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 1.65 \text{ V}$	1.2		-	1.2	-	V
		$I_{O} = -9 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 2.3 \text{ V}$	1.75		-	1.75	-	V
		$I_{O} = -12 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 3.0 \text{ V}$	2.3		-	2.3	-	V

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Static characteristics ...continued[1][2] Table 8.

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	bol Parameter Conditions -40 °C to +85 °		o +85 °C	–40 °C to +125 °C		Unit		
				Min	Мах	Min	Max	-
V _{OL}	LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}$						
	output voltage	$ I_O = 100 \ \mu A; \\ V_{CC(A)} = V_{CC(B)} = 0.8 \ V \ to \ 3.6 \ V $		-	0.1	-	0.1	V
		$I_O = 3 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 1.1 \text{ V}$		-	0.25	-	0.25	V
		$I_{O} = 6 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 1.4 \text{ V}$		-	0.35	-	0.35	V
		$I_{O} = 8 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 1.65 \text{ V}$		-	0.45	-	0.45	V
		$\label{eq:loss} \begin{array}{l} I_O = 9 \text{ mA}; \\ V_{CC(A)} = V_{CC(B)} = 2.3 \text{ V} \end{array}$		-	0.55	-	0.55	V
		$\label{eq:loss} \begin{array}{l} I_{O} = 12 \text{ mA}; \\ V_{CC(A)} = V_{CC(B)} = 3.0 \text{ V} \end{array}$		-	0.7	-	0.7	V
l _l	input leakage current	nDIR, n $\overline{\text{OE}}$ input; V _I = 0 V or 3.6 V; V _{CC(A)} = V _{CC(B)} = 0.8 V to 3.6 V		-	±1	-	±5	μA
I _{BHL}	bus hold	A or B port	<u>[3]</u>					
	LOW current	V _I = 0.49 V; V _{CC(A)} = V _{CC(B)} = 1.4 V		15	-	15	-	μA
		V _I = 0.58 V; V _{CC(A)} = V _{CC(B)} = 1.65 V		25	-	25	-	μA
		V _I = 0.70 V; V _{CC(A)} = V _{CC(B)} = 2.3 V		45	-	45	-	μA
		$V_{I} = 0.80 \text{ V};$ $V_{CC(A)} = V_{CC(B)} = 3.0 \text{ V}$		100	-	90	-	μA
I _{BHH}	bus hold	A or B port	<u>[4]</u>					
	HIGH current	$V_{I} = 0.91 \text{ V};$ $V_{CC(A)} = V_{CC(B)} = 1.4 \text{ V}$		-15	-	-15	-	μA
		V _I = 1.07 V; V _{CC(A)} = V _{CC(B)} = 1.65 V		-25	-	-25	-	μA
		$V_{I} = 1.60 V;$ $V_{CC(A)} = V_{CC(B)} = 2.3 V$		-45	-	-45	-	μΑ
		V _I = 2.00 V; V _{CC(A)} = V _{CC(B)} = 3.0 V		-100	-	-100	-	μA
I _{BHLO}	bus hold	A or B port	<u>[5]</u>					
	LOW	$V_{CC(A)} = V_{CC(B)} = 1.6 \text{ V}$		125	-	125	-	μΑ
	current	$V_{CC(A)} = V_{CC(B)} = 1.95 \text{ V}$		200	-	200	-	μΑ
		$V_{CC(A)} = V_{CC(B)} = 2.7 \text{ V}$		300	-	300	-	μA
		$V_{CC(A)} = V_{CC(B)} = 3.6 \text{ V}$		500	-	500	-	μA
I _{BHHO}	bus hold	A or B port	<u>[6]</u>					
	HIGH	$V_{CC(A)} = V_{CC(B)} = 1.6 V$		-125	-	-125	-	μA
	current	$V_{CC(A)} = V_{CC(B)} = 1.95 V$		-200	-	-200	-	μA
		$V_{CC(A)} = V_{CC(B)} = 2.7 V$		-300	-	-300	-	μA
		$V_{CC(A)} = V_{CC(B)} = 3.6 \text{ V}$		-500	-	-500	-	μA

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Unit

μA

μA

μA

μΑ

μA

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At recommended operating conditions; voltages are referenced to GND (ground = 0 V). Symbol Parameter Conditions -40 °C to +85 °C -40 °C to +125 °C Min Max Min Max **OFF-state** A or B port; $V_0 = 0$ V or V_{CCO} ; [7] ±30 ±5 I_{OZ} _ _ output $V_{CC(A)} = V_{CC(B)} = 3.6 V$ current suspend mode A port; [7] ±30 ±5 -- $V_{O} = 0 V \text{ or } V_{CCO}; V_{CC(A)} = 3.6 V;$ $V_{CC(B)} = 0 V$ suspend mode B port; [7] ± 30 ±5 --A port; V_{I} or $V_{O} = 0$ V to 3.6 V; power-off ±5 ±30 IOFF -leakage $V_{CC(A)} = 0 V;$ current $V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$ B port; V_1 or $V_0 = 0$ V to 3.6 V; ±5 ±30 _ _ $V_{CC(B)} = 0 V;$ $V_{CC(A)} = 0.8 \text{ V to } 3.6 \text{ V}$

Static characteristics ... continued[1][2] Table 8.

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Symbol Parameter		Conditions	–40 °C	to +85 °C	–40 °C to	o +125 ℃	Unit
			Min	Max	Min	Max	
I _{CC}	supply	A port; $V_I = 0$ V or V_{CCI} ; $I_O = 0$ A					
	current	$V_{CC(A)} = 0.8 V \text{ to } 3.6 V;$ $V_{CC(B)} = 0.8 V \text{ to } 3.6 V$	-	10	-	55	μΑ
		$V_{CC(A)} = 1.1 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	8	-	50	μΑ
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(B)} = 0 \text{ V}$	-	8	-	50	μA
		$V_{CC(A)} = 0 V; V_{CC(B)} = 3.6 V$	-2	-	-12	-	μA
		B port; $V_I = 0$ V or V_{CCI} ; $I_O = 0$ A					
		$V_{CC(A)} = 0.8 V \text{ to } 3.6 V;$ $V_{CC(B)} = 0.8 V \text{ to } 3.6 V$	-	10	-	55	μΑ
		$V_{CC(A)} = 1.1 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	8	-	50	μΑ
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(B)} = 0 \text{ V}$	-2	-	-12	-	μA
		$V_{CC(A)} = 0 V; V_{CC(B)} = 3.6 V$	-	8	-	50	μA
			-	20	-	70	μA
			-	16	-	65	μA

Table 8. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

[1] V_{CCO} is the supply voltage associated with the output port.

[2] V_{CCI} is the supply voltage associated with the data input port.

- [3] The bus hold circuit can sink at least the minimum low sustaining current at V_{IL} max. I_{BHL} should be measured after lowering V_I to GND and then raising it to V_{IL} max.
- [4] The bus hold circuit can source at least the minimum high sustaining current at V_{IH} min. I_{BHH} should be measured after raising V_I to V_{CC} and then lowering it to V_{IH} min.
- [5] An external driver must source at least $I_{\mbox{\scriptsize BHLO}}$ to switch this node from LOW to HIGH.
- [6] An external driver must sink at least I_{BHHO} to switch this node from HIGH to LOW.
- [7] For I/O ports, the parameter I_{OZ} includes the input leakage current.

Table 9.	Typical total	supply current ((I _{CC(A)} +	I _{CC(B)})
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V _{CC(A)}	V _{CC(B)}			l l l l l l l l l l l l l l l l l l l				
	0 V	0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	
0 V	0	0.1	0.1	0.1	0.1	0.1	0.1	μΑ
0.8 V	0.1	0.1	0.1	0.1	0.1	0.3	1.6	μΑ
1.2 V	0.1	0.1	0.1	0.1	0.1	0.1	0.8	μΑ
1.5 V	0.1	0.1	0.1	0.1	0.1	0.1	0.4	μΑ
1.8 V	0.1	0.1	0.1	0.1	0.1	0.1	0.2	μΑ
2.5 V	0.1	0.3	0.1	0.1	0.1	0.1	0.1	μΑ
3.3 V	0.1	1.6	0.8	0.4	0.2	0.1	0.1	μΑ

11. Dynamic characteristics

Table 10. Typical power dissipation capacitance at $V_{CC(A)} = V_{CC(B)}$ and $T_{amb} = 25 \text{ °C}$ [1][2] *Voltages are referenced to GND (ground = 0 V).*

Symbol	Parameter	Conditions			V _{CC(A)} :	= V _{CC(B)}			Unit
			0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	
C _{PD} power dissipation capacitance	A port: (direction nAn to nBn); output enabled	0.2	0.2	0.2	0.2	0.3	0.4	pF	
	A port: (direction nAn to nBn); output disabled	0.2	0.2	0.2	0.2	0.3	0.4	pF	
	A port: (direction nBn to nAn); output enabled	9.5	9.7	9.8	9.9	10.7	11.9	pF	
		A port: (direction nBn to nAn); output disabled	0.6	0.6	0.6	0.6	0.7	0.7	pF
		B port: (direction nAn to nBn); output enabled	9.5	9.7	9.8	9.9	10.7	11.9	pF
		B port: (direction nAn to nBn); output disabled	0.6	0.6	0.6	0.6	0.7	0.7	pF
		B port: (direction nBn to nAn); output enabled	0.2	0.2	0.2	0.2	0.3	0.4	pF
		B port: (direction nBn to nAn); output disabled	0.2	0.2	0.2	0.2	0.3	0.4	pF

[1] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \Sigma(C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$

 f_i = input frequency in MHz;

 $f_o = output frequency in MHz;$

 C_L = load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}{}^2 \times f_o)$ = sum of the outputs.

[2] $f_i = 10 \text{ MHz}$; $V_I = \text{GND}$ to V_{CC} ; $t_r = t_f = 1 \text{ ns}$; $C_L = 0 \text{ pF}$; $R_L = \infty \Omega$.

vonages										
Symbol Parame	Parameter	Conditions	V _{CC(B)}							
			0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V		
t _{pd} propagation delay	nAn to nBn	14.5	7.3	6.5	6.2	5.9	6.0	ns		
		nBn to nAn	14.5	12.7	12.4	12.3	12.1	12.0	ns	
t _{dis}	disable time	nOE to nAn	14.3	14.3	14.3	14.3	14.3	14.3	ns	
		nOE to nBn	17.0	9.9	9.0	9.4	9.0	9.7	ns	
t _{en}	enable time	nOE to nAn	18.2	18.2	18.2	18.2	18.2	18.2	ns	
		nOE to nBn	19.2	10.7	9.8	9.6	9.7	10.2	ns	

Table 11. Typical dynamic characteristics at $V_{CC(A)} = 0.8 V$ and $T_{amb} = 25 \circ C$ [1] Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9; for wave forms see Figure 7 and Figure 8

[1] t_{pd} is the same as t_{PLH} and t_{PHL} ; t_{dis} is the same as t_{PLZ} and t_{PHZ} ; t_{en} is the same as t_{PZL} and t_{PZH} .

Table 12. Typical dynamic characteristics at $V_{CC(B)} = 0.8$ V and $T_{amb} = 25$ °C [1]

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9; for wave forms see Figure 7 and Figure 8

Symbol	Parameter	conditions V _{CC(A)}					A)			
			0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V		
t _{pd}	t _{pd} propagation delay	nAn to nBn	14.5	12.7	12.4	12.3	12.1	12.0	ns	
		nBn to nAn	14.5	7.3	6.5	6.2	5.9	6.0	ns	
t _{dis}	disable time	nOE to nAn	14.3	5.5	4.1	4.0	3.0	3.5	ns	
		nOE to nBn	17.0	13.8	13.4	13.1	12.9	12.7	ns	
t _{en}	enable time	nOE to nAn	18.2	5.6	4.0	3.2	2.4	2.2	ns	
		nOE to nBn	19.2	14.6	14.1	13.9	13.7	13.6	ns	

[1] t_{pd} is the same as t_{PLH} and t_{PHL} ; t_{dis} is the same as t_{PLZ} and t_{PHZ} ; t_{en} is the same as t_{PZL} and t_{PZH} .

Symbol	Parameter	Conditions		,,		<u></u>	Vc	C(P)		<u></u>		.gu. o o	Unit
0,111,501	, aramotor	Contaitone	12V-	-01V	15V-	+01V	18V+	0 15 V	25V-	+02V	33V-	+03V	
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	-
Vec(a) =	1.1 V to 1.3 V			max		max		max		max		max	
• CC(A) -	propagation	nAn to nBn	0.5	9.4	0.5	7.1	0.5	6.2	0.5	5.2	0.5	5.1	ns
-pu	delay	nBn to nAn	0.5	9.4	0.5	8.9	0.5	8.7	0.5	8.4	0.5	8.2	ns
t _{die}	disable time	nOE to nAn	1.8	10.9	1.8	10.9	1.8	10.9	1.8	10.9	1.8	10.9	ns
1013		nOE to nBn	1.9	12.4	1.9	9.6	1.9	9.5	1.4	8.1	1.2	9.1	ns
t _{en}	enable time	nOE to nAn	1.4	12.8	1.4	12.8	1.4	12.8	1.4	12.8	1.4	12.8	ns
	nOE to nBn	1.1	13.3	1.1	10.0	1.1	8.9	1.0	7.9	1.0	7.7	ns	
$V_{CC(A)} =$	1.4 V to 1.6 V												
t _{pd}	propagation	nAn to nBn	0.3	8.9	0.3	6.3	0.3	5.2	0.3	4.2	0.3	4.2	ns
F-	delay	nBn to nAn	0.7	7.1	0.7	6.3	0.5	6.0	0.4	5.7	0.3	5.6	ns
t _{dis}	disable time	nOE to nAn	1.8	10.2	1.8	10.2	1.5	10.2	1.3	10.2	1.6	10.2	ns
		nOE to nBn	1.9	11.3	1.9	10.3	1.9	9.1	1.4	7.4	1.2	7.6	ns
t _{en}	enable time	nOE to nAn	1.1	9.4	1.4	9.4	1.1	9.4	0.7	9.4	0.4	9.4	ns
		nOE to nBn	1.4	12.1	1.4	9.6	1.1	7.7	0.9	5.8	0.9	5.6	ns
$V_{CC(A)} =$	1.65 V to 1.95	V											
t _{pd}	propagation	nAn to nBn	0.1	8.7	0.1	6.0	0.1	4.9	0.1	3.9	0.3	3.9	ns
	delay	nBn to nAn	0.6	6.2	0.6	5.3	0.5	4.9	0.3	4.6	0.3	4.5	ns
t _{dis}	disable time	nOE to nAn	1.8	8.6	1.6	8.6	1.8	8.6	1.3	8.6	1.6	8.6	ns
		nOE to nBn	1.7	10.9	1.7	9.9	1.6	8.7	1.2	6.9	1.0	6.9	ns
t _{en}	enable time	nOE to nAn	1.0	7.2	1.0	7.2	1.0	7.2	0.6	7.2	0.4	7.2	ns
		nOE to nBn	1.2	11.7	1.2	9.2	1.0	7.4	0.8	5.3	0.8	4.6	ns
$V_{CC(A)} =$	2.3 V to 2.7 V												
t _{pd}	propagation	nAn to nBn	0.1	8.4	0.1	5.7	0.1	4.6	0.2	3.5	0.1	3.6	ns
	delay	nBn to nAn	0.6	5.2	0.6	4.2	0.4	3.9	0.2	3.4	0.2	3.3	ns
t _{dis}	disable time	nOE to nAn	1.0	6.2	1.0	6.2	1.0	6.2	1.0	6.2	1.0	6.2	ns
		nOE to nBn	1.5	10.4	1.5	8.8	1.3	8.2	1.1	6.2	0.9	5.2	ns
t _{en}	enable time	nOE to nAn	0.7	4.8	0.7	4.8	0.7	4.8	0.6	4.8	0.4	4.8	ns
		nOE to nBn	0.9	11.3	0.9	8.8	0.8	7.0	0.6	4.8	0.6	4.0	ns
$V_{CC(A)} =$	3.0 V to 3.6 V				1					1			
t _{pd}	propagation	nAn to nBn	0.1	8.2	0.1	5.6	0.1	4.5	0.1	3.3	0.1	2.9	ns
	delay	nBn to nAn	0.6	5.1	0.6	4.2	0.4	3.4	0.2	3.0	0.1	2.8	ns
t _{dis}	disable time	nOE to nAn	0.7	5.6	0.7	5.6	0.7	5.6	0.7	5.6	0.7	5.6	ns
		nOE to nBn	1.4	10.2	1.4	9.3	1.2	8.1	1.0	6.4	0.8	6.2	ns
t _{en}	enable time	nOE to nAn	0.6	3.8	0.6	3.8	0.6	3.8	0.6	3.8	0.4	3.8	ns
	nOE to nBn	0.8	11.3	0.8	8.7	0.6	6.8	0.5	4.7	0.5	3.8	ns	

Table 13. Dynamic characteristics for temperature range $-40 \degree$ C to $+85 \degree$ C [1]Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9; for wave forms see Figure 7 and Figure 8.

[1] t_{pd} is the same as t_{PLH} and t_{PHL} ; t_{dis} is the same as t_{PLZ} and t_{PHZ} ; t_{en} is the same as t_{PZL} and t_{PZH} .

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Symbol	Parameter	Conditions		,, 10/ 100	n on oun	<u></u>	<u>Vc</u>	(D)		e <u>rigare</u>		iguro o	Unit
e y moet	, arameter	Contaitions	12V-	+01V	15V-	+01V	18V+	0 15 V	25V-	+02V	33V-	+03V	•••••
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	-
$V_{CC(A)} =$	1.1 V to 1.3 V			max		max		max		max		Шах	
t _{nd}	propagation	nAn to nBn	0.5	10.4	0.5	7.9	0.5	6.9	0.5	5.8	0.5	5.7	ns
pu	delay	nBn to nAn	0.5	10.4	0.5	9.8	0.5	9.6	0.5	9.3	0.5	9.1	ns
t _{dis}	disable time	nOE to nAn	1.8	12.0	1.8	12.0	1.8	12.0	1.8	12.0	1.8	12.0	ns
		nOE to nBn	1.9	13.7	1.9	10.6	1.9	10.5	1.4	9.0	1.2	10.1	ns
t _{en}	enable time	nOE to nAn	1.4	14.1	1.4	14.1	1.4	14.1	1.4	14.1	1.4	14.1	ns
		nOE to nBn	1.1	14.7	1.1	11.0	1.1	9.8	1.0	8.7	1.0	8.5	ns
V _{CC(A)} =	1.4 V to 1.6 V		1	1	1	1				1	1		
t _{pd}	propagation	nAn to nBn	0.3	9.8	0.3	7.0	0.3	5.8	0.3	4.7	0.3	4.7	ns
	delay	nBn to nAn	0.7	7.9	0.7	7.0	0.5	6.6	0.4	6.3	0.3	6.2	ns
t _{dis}	disable time	nOE to nAn	1.8	11.3	1.8	11.3	1.5	11.3	1.3	11.3	1.6	11.3	ns
		nOE to nBn	1.9	12.5	1.9	11.4	1.9	10.1	1.4	8.2	1.2	8.4	ns
t _{en}	enable time	nOE to nAn	1.1	10.4	1.4	10.4	1.1	10.4	0.7	10.4	0.4	10.4	ns
		nOE to nBn	1.4	13.3	1.4	10.6	1.1	8.5	0.9	6.4	0.9	6.2	ns
$V_{CC(A)} =$	1.65 V to 1.95	V											
t _{pd}	propagation	nAn to nBn	0.1	9.6	0.1	6.6	0.1	5.4	0.1	4.3	0.3	4.3	ns
	delay	nBn to nAn	0.6	6.9	0.6	5.9	0.5	5.4	0.3	5.1	0.3	5.0	ns
t _{dis}	disable time	nOE to nAn	1.8	9.5	1.6	9.5	1.8	9.5	1.3	9.5	1.6	9.5	ns
		nOE to nBn	1.7	12.0	1.7	10.9	1.6	9.6	1.2	7.6	1.0	7.6	ns
t _{en}	enable time	nOE to nAn	1.0	8.0	1.0	8.0	1.0	8.0	0.6	8.0	0.4	8.0	ns
		nOE to nBn	1.2	12.9	1.2	10.2	1.0	8.2	0.8	5.9	0.8	5.1	ns
$V_{CC(A)} =$	2.3 V to 2.7 V	1											
t _{pd}	propagation	nAn to nBn	0.1	9.3	0.1	6.3	0.1	5.1	0.2	4.0	0.1	4.0	ns
	uelay	nBn to nAn	0.6	5.8	0.6	4.7	0.4	4.3	0.2	3.9	0.2	3.8	ns
t _{dis}	disable time	nOE to nAn	1.0	6.9	1.0	6.9	1.0	6.9	1.0	6.9	1.0	6.9	ns
		nOE to nBn	1.5	11.5	1.5	10.4	1.3	9.1	1.1	6.9	0.9	5.8	ns
t _{en}	enable time	nOE to nAn	0.7	5.3	0.7	5.3	0.7	5.3	0.6	5.3	0.4	5.3	ns
		nOE to nBn	0.9	12.4	0.9	9.7	0.8	7.7	0.6	5.3	0.6	4.4	ns
$V_{CC(A)} =$	3.0 V to 3.6 V		1	1	1	1				1			
t _{pd}	propagation	nAn to nBn	0.1	9.1	0.1	6.2	0.1	5.0	0.1	3.8	0.1	3.3	ns
	uelay	nBn to nAn	0.6	5.7	0.6	4.7	0.4	3.9	0.2	3.4	0.1	3.3	ns
t _{dis}	disable time	nOE to nAn	0.7	6.2	0.7	6.2	0.7	6.2	0.7	6.2	0.7	6.2	ns
		nOE to nBn	1.4	11.3	1.4	10.3	1.2	9.0	1.0	7.1	0.8	6.9	ns
t _{en}	enable time	nOE to nAn	0.6	4.2	0.6	4.2	0.6	4.2	0.6	4.2	0.4	4.2	ns
	nOE to nBn	0.8	12.4	0.8	9.6	0.6	7.5	0.5	5.2	0.5	4.2	ns	

Table 14. Dynamic characteristics for temperature range $-40 \degree$ C to $+125 \degree$ C [1] Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9; for wave forms see Figure 7 and Figure 8

[1] t_{pd} is the same as t_{PLH} and t_{PHL} ; t_{dis} is the same as t_{PLZ} and t_{PHZ} ; t_{en} is the same as t_{PZL} and t_{PZH} .

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12. Waveforms





Table 15.Measurement points

Supply voltage	Input ^[1]	Output ^[2]		
V _{CC(A)} , V _{CC(B)}	V _M	V _M	V _X	V _Y
0.8 V to 1.6 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.1 V	V _{OH} – 0.1 V
1.65 V to 2.7 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.15 V	V _{OH} – 0.15 V
3.0 V to 3.6 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.3 V	V _{OH} – 0.3 V

[1] V_{CCI} is the supply voltage associated with the data input port.

[2] V_{CCO} is the supply voltage associated with the output port.

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Table 16. Test data

Supply voltage Input		Load					
V _{CC(A)} , V _{CC(B)}	V _I [1]	∆t/∆V <mark>[2]</mark>	CL	R _L	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ} [3]
0.8 V to 1.6 V	V _{CCI}	\leq 1.0 ns/V	15 pF	2 kΩ	open	GND	2V _{CCO}
1.65 V to 2.7 V	V _{CCI}	\leq 1.0 ns/V	15 pF	2 kΩ	open	GND	2V _{CCO}
3.0 V to 3.6 V	V _{CCI}	\leq 1.0 ns/V	15 pF	2 kΩ	open	GND	2V _{CCO}

[1] V_{CCI} is the supply voltage associated with the data input port.

[3] V_{CCO} is the supply voltage associated with the output port.

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13. Typical propagation delay characteristics

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a. LOW to HIGH propagation delay (nAn to nBn); $V_{CC(A)}$ = 1.2 V



- c. LOW to HIGH propagation delay (nAn to nBn); $V_{CC(A)} = 1.5 \text{ V}$
- (1) $V_{CC(B)} = 1.2$ V.
- (2) V_{CC(B)} = 1.5 V.
- (3) $V_{CC(B)} = 1.8$ V.
- (4) $V_{CC(B)} = 2.5 V.$
- (5) $V_{CC(B)} = 3.3 V.$

Fig 11. Typical propagation delay versus load capacitance; T_{amb} = 25 °C



b. HIGH to LOW propagation delay (nAn to nBn); $V_{CC(A)} = 1.2 \text{ V}$



d. HIGH to LOW propagation delay (nAn to nBn); $V_{CC(A)} = 1.5 \text{ V}$

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a. LOW to HIGH propagation delay (nAn to nBn); $V_{CC(A)}$ = 1.8 V



- c. LOW to HIGH propagation delay (nAn to nBn); $V_{CC(A)}$ = 2.5 V
- (1) $V_{CC(B)} = 1.2$ V.
- (2) V_{CC(B)} = 1.5 V.
- (3) $V_{CC(B)} = 1.8$ V.
- (4) $V_{CC(B)} = 2.5 V.$
- (5) $V_{CC(B)} = 3.3$ V.

Fig 12. Typical propagation delay versus load capacitance; T_{amb} = 25 °C



b. HIGH to LOW propagation delay (nAn to nBn); $V_{CC(A)} = 1.8 \text{ V}$



d. HIGH to LOW propagation delay (nAn to nBn); $V_{CC(A)} = 2.5 \text{ V}$

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14. Package outline



Fig 14. Package outline SOT109-1 (SO16)

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Fig 15. Package outline SOT403-1 (TSSOP16)

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DHVQFN16: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 x 3.5 x 0.85 mm SOT763-1

Fig 16. Package outline SOT763-1 (DHVQFN16)

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XQFN16: plastic, extremely thin quad flat package; no leads; 16 terminals; body 1.80 x 2.60 x 0.50 mm

Fig 17. Package outline SOT1161-1 (XQFN16)

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15. Abbreviations

Table 17. Abbreviations					
Acronym	Description				
CDM	Charged Device Model				
DUT	Device Under Test				
ESD	ElectroStatic Discharge				
НВМ	Human Body Model				
MM	Machine Model				

16. Revision history

Table 18.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
74AVCH4T245 v.5	20151217	Product data sheet	-	74AVCH4T245 v.4	
Modifications: • Table 5: conditions I _{CC} and I _{GND} changed (errata).					
74AVCH4T245 v.4	20111214	Product data sheet		74AVCH4T245 v.3	
Modifications:	 Legal pages u 	pdated.			
74AVCH4T245 v.3	20110927	Product data sheet	-	74AVCH4T245 v.2	
74AVCH4T245 v.2	20101203	Product data sheet	-	74AVCH4T245 v.1	
74AVCH4T245 v.1	20090806	Product data sheet	-	-	

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17. Legal information

17.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nexperia.com.

17.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. Nexperia does not give any

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